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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
YOR920030334US1

In Re Application Of: **Ricky S. Amos et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/786,901	February 25, 2004	Asok K. Sarkar	23389	2891	6726

Title: **CMOS SILICIDE METAL GATE INTEGRATION DESCRIPTION**



Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

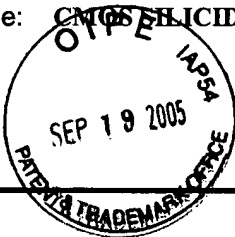
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(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
YOR920030334US1

In Re Application of: **Ricky S. Amos et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/786,901	February 25, 2004	Asok K. Sarkar	23389	2891	6726

Title: **CYTOFLICIDE METAL GATE INTEGRATION DESCRIPTION**



Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0510** as described below.
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Dated: September 16, 2005

Leslie S. Szivos, Ph.D.

Reg. No. 39,394

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CC:



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Ricky S. Amos et al.

Examiner: Asok K. Sarkar

Serial No.: 10/786,901

Art Unit: 2891

Filed: February 25, 2004

Docket: YOR920030334US1 (16899)

For: CMOS SILICIDE METAL GATE
INTEGRATION DESCRIPTION

Dated: September 16, 2005

Confirmation No. 6726

Mailstop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

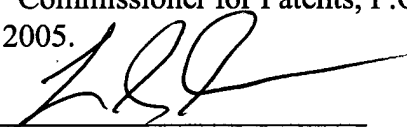
In accordance with 37 C.F.R §§1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. Oh J. et al. "Interdigitated Ge p-i-n Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers." *IEEE Journal of Quantum Electronics*, vol. 38, no. 9, (2002);
2. Jones R.E. et al. "Fabrication and Modeling of Gigahertz Photodetectors in Heteroepitaxial Ge-on-Si Using a Graded Buffer Layer Deposited by Low Energy Plasma Enhanced CVD." *IEDM* p793 (2002); and

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on September 16, 2005.

Dated: September 16, 2005



Leslie S. Szivos, Ph.D.

3. United States Patent Application Publication No. 2003/0141565, dated July 31, 2003, issued to Hirose et al.

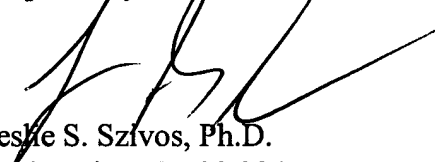
The references were cited in a Search Report dated August 18, 2005 received from the European Patent Office in connection with the corresponding PCT application. Applicants are submitting copies of the above-cited non-US references, together with a copy of the Search Report. The relevance of the above-identified references has been described in the Search Report.

In accordance with the waiver of 37 C.F.R. § 1.98 (a)(2)(i), per 1276 OG 55, August 5, 2003, applicants are not required to submit copies of the above-cited U.S. Patent references. Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

In the event that an action on the merits crosses in the mail when submitting this Information Disclosure Statement, applicants hereby state

“That each item of information contained herein was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.”

Respectfully submitted,

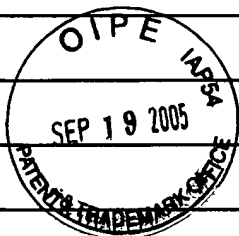


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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) YOR920030334US1 (16899)		Application Number 10/786,901	
	Applicant(s) Ricky S. Amos et al.			
	Filing Date February 25, 2004		Group Art Unit 2891	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE



U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2003/0141565 A1	7/31/2003	Hirose et al.			

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
		Oh J. et al. "Interdigitated Ge p-i-n Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers." IEEE Journal of Quantum Electronics, vol. 38, no. 9, (2002)
		Jones R.E. et al. "Fabrication and Modeling of Gigahertz Photodetectors in Heteroepitaxial Ge-on-Si Using a Graded Buffer Layer Deposited by Low Energy Plasma Enhanced CVD." IEDM p793 (2002)

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.